

6. (Amended) The process of Claim 1 which includes a further step of adhering a second semiconductor die with a second adhesive film thereon to said substrate at a position laterally removed from the first die.

Sub  
Cat  
1

12. (New) A method of manufacturing a semiconductor device comprising the steps of:  
providing a wafer with a plurality of spaced apart semiconductor elements;  
placing a thin flexible film, which is separate from said wafer, and said wafer atop one another to form a film/wafer structure;  
preheating said film/wafer structure to partially cure said thin flexible film, thereby forming adhesion between said thin flexible film and said wafer;  
singulating said film/wafer structure with said partially cured thin flexible film, thereby forming a plurality of individual semiconductor dies;  
placing at least one individual semiconductor die with said partially cured thin flexible film, which faces a substrate, on the said substrate; and  
heating said individual semiconductor die and said partially cured thin film to fully cure said thin flexible film, thereby bonding said individual semiconductor die with said substrate.